DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

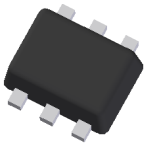
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Mechanical Data

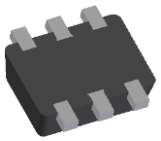
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT563

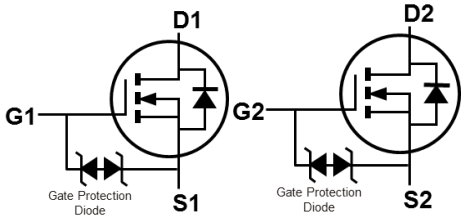
ESD PROTECTED



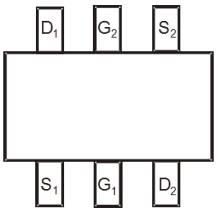
Top View



Bottom View



Internal Schematic



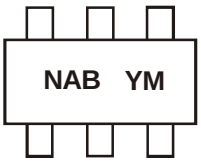
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2004VK-7	SOT563	3000/Tape & Reel
DMN2004VK-7B	SOT563	8000/Tape & Reel (Note 5)
DMN2004VK-13	SOT563	10000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
5. Change the pitch from 4mm to 2mm in T& R.

Marking Information



NAB = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2010	…	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	X	…	G	H	I	J	K	L	M	N	O	P

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Drain Current (Note 6)	Steady State	T_A = +25°C T_A = +85°C	I_D	540 390	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	1.5	A

Thermal Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 10µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 16V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.4 0.5 0.7	0.55 0.70 0.9	Ω	V_{GS} = 4.5V, I_D = 540mA V_{GS} = 2.5V, I_D = 500mA V_{GS} = 1.8V, I_D = 350mA
Forward Transfer Admittance	$\|Y_{fs}\|$	200	—	—	ms	V_{DS} =10V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	—	150	pF	V_{DS} = 16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	20	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	$t_{D(ON)}$	—	8.0	—	ns	V_{DD} = 10V, R_L = 47Ω, I_D = 200mA. V_{GEN} = 4.5V, R_G = 10Ω
Rise Time	t_R	—	13.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	53.5	—	ns	
Fall Time	t_F	—	36.1	—	ns	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

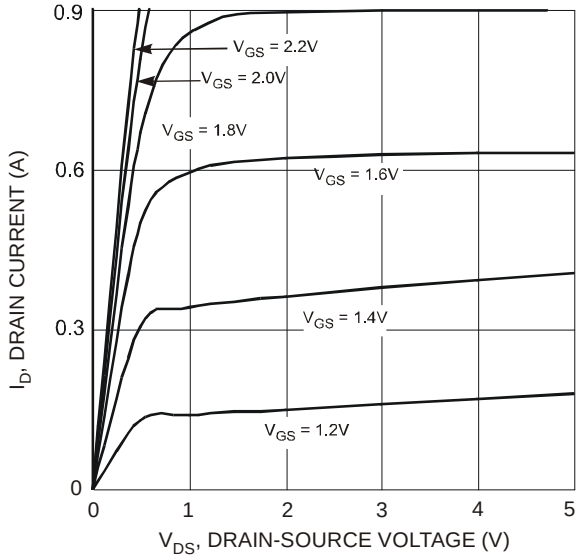


Fig. 1 Typical Output Characteristics

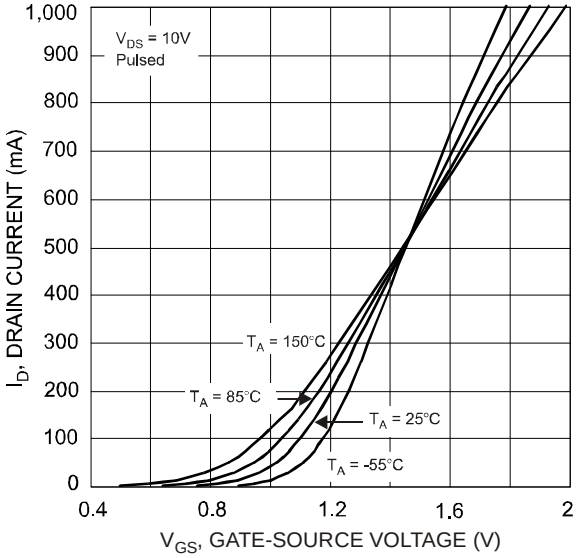


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

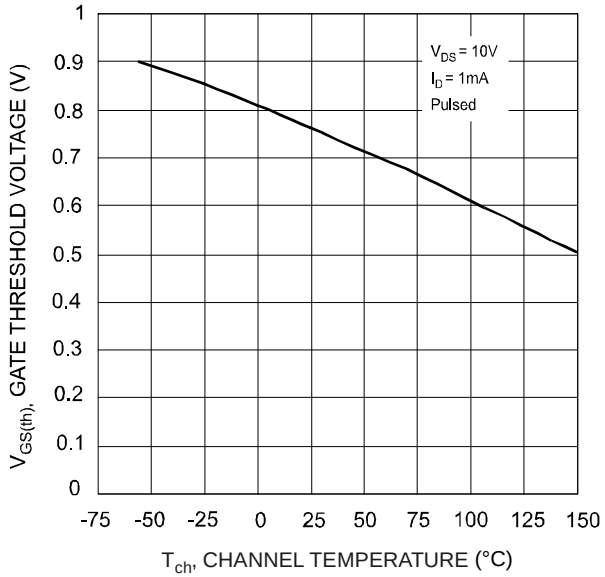


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

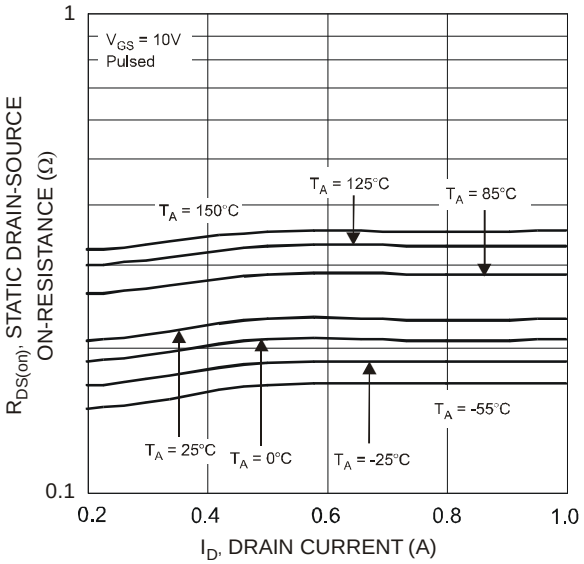


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

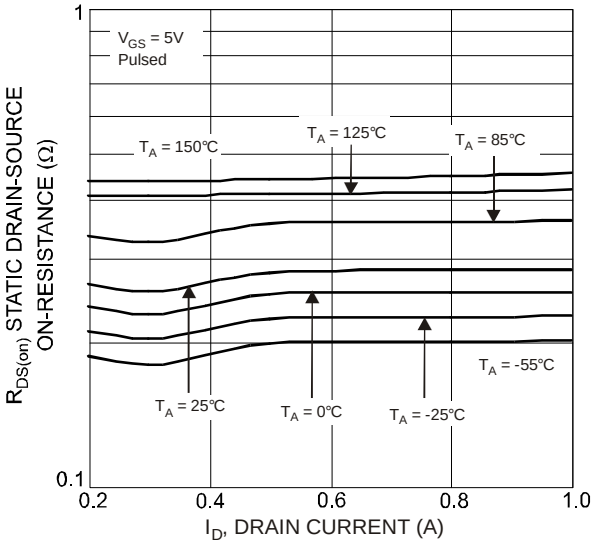


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

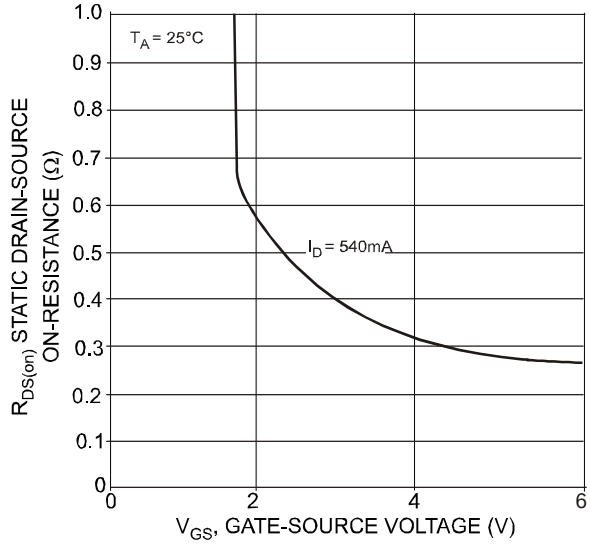


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage

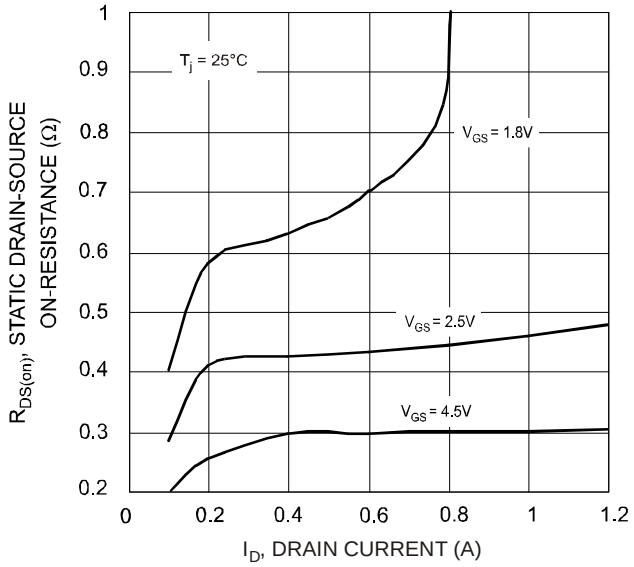


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage

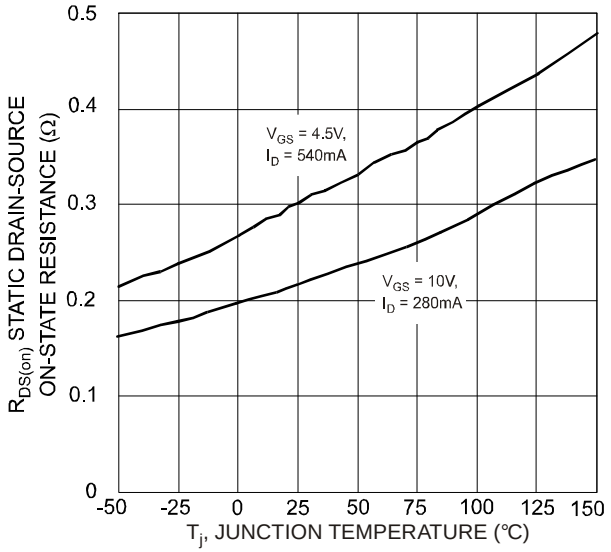


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

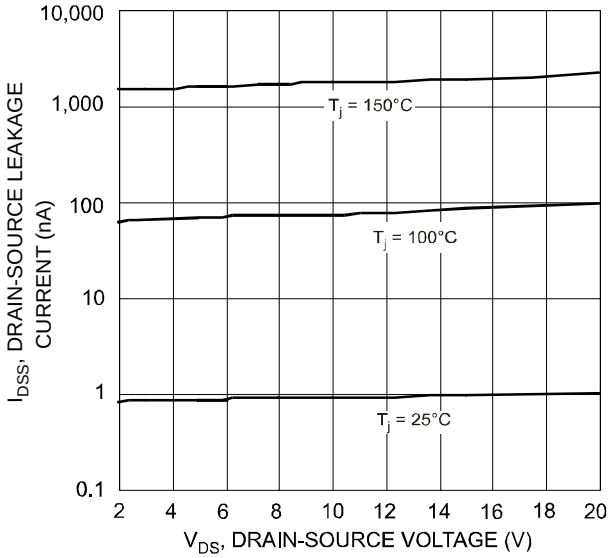


Fig. 9 Drain Source Leakage Current vs. Voltage

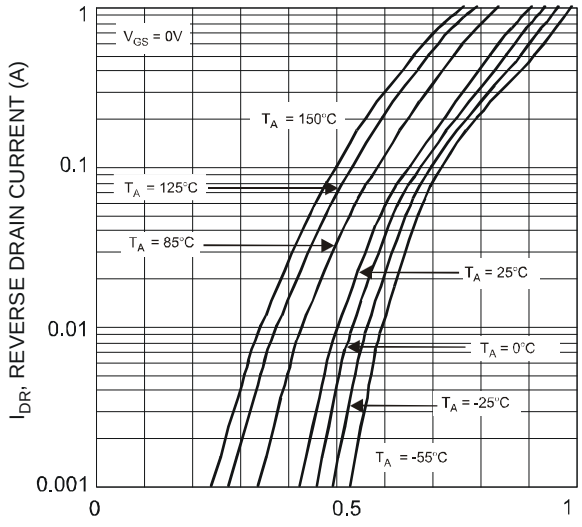


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

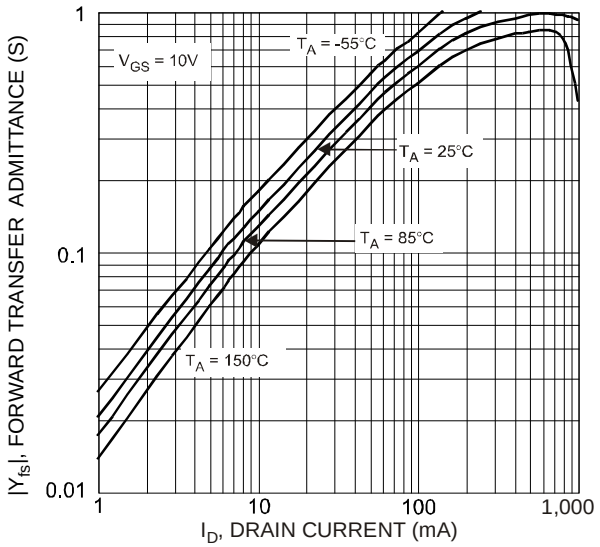


Fig. 11 Forward Transfer Admittance vs. Drain Current

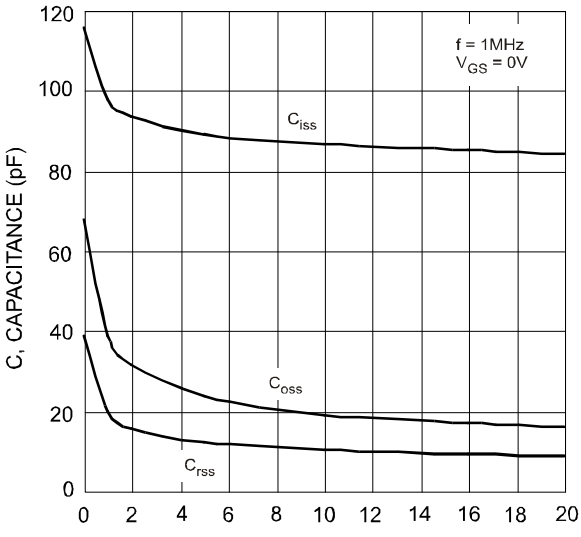
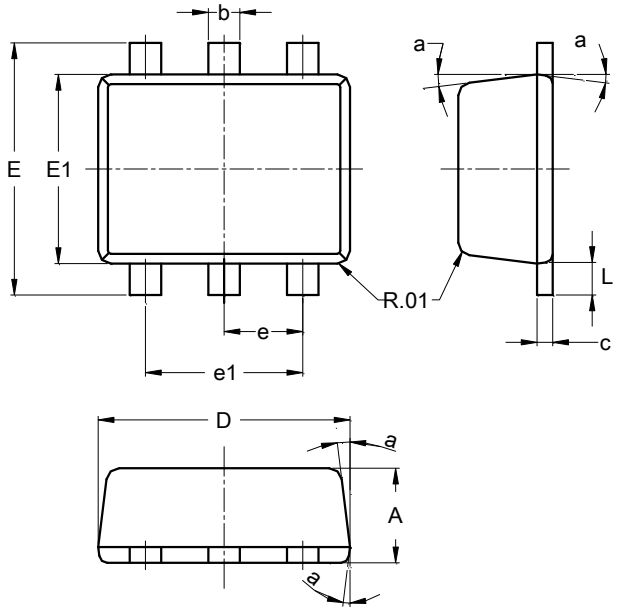


Fig. 12 Capacitance Variation

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563

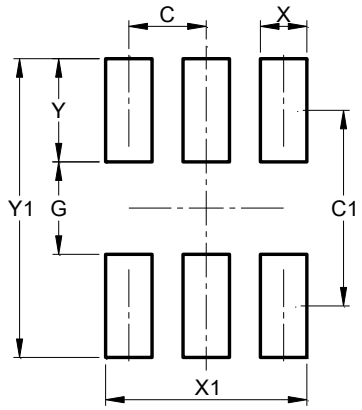


SOT563			
Dim	**Min**	**Max**	**Typ**
A	0.55	0.60	0.60
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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